

**99-0205**

The invention relates to photonics, particularly, to the semiconductor photodetectors.

The photodetector is made on a dielectric base, onto which there are applied in series the first semitransparent contacting electrode, the photosensitive layer of chalcogenic vitreous semiconductor arsenic-selenium, doped with tin of the formula  $(AsSe)_{100-x} : Sn_x$ , where  $7,5 \leq x \leq 10,0\%$  at., and the second semitransparent contacting electrode.